



## PNP EPITAXIAL SILICON TRANSISTOR (Version C1.0)

S9015

General Purpose Application

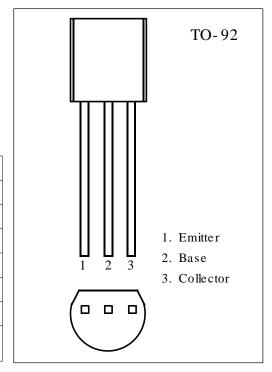
Switching Application

- ♦ Collector Current Ic=-100mA
- ♦ Collector Power Dissipation Pc=450mW
- ♦ Complementary to S9014

## ABSOLUTE MAXIMUM RATINGS

 $(Ta=25^{\circ}C)$ 

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	VCBO	-50	V	
Collector-Emitter Voltage	VCEO	-45	V	
Emitter-Base voltage	VEBO	-5	V	
Collector Current	IC	-100	mA	
Collector Power Dissipation	PC	450	mW	
Junction Temperature	Tj	150	Õ	
Storage Temperature	Tstg	-55~ +150	°C	



## **ELECTRICAL CHARACTERISTICS**

(Ta=25°C unless otherwise specified)

Characteristic	Symbol	Test Condition	Min	Тур	Max	Unit
Collector-base breakdown voltage	ВУсво	Ic=-100μA	-50			V
Collector-emitter breakdown voltage	BVCEO	IC=-1 mA	-45			V
Emitter-base breakdown voltage	ВУЕВО	I <sub>E</sub> =-100μA	-5			V
Collector cut-off current	Ісво	V <sub>CB</sub> =-50V			-50	nA
DC current gain	hFE	IC=-1mA VCE=-5V	60		600	
Collector-emitter saturation voltage	VCE(sat)	IC=-100mA IB=- 5mA			-0.7	V

<sup>\*</sup> hFE Classification: A:60~150, B:100~300 , C:200~600 , D=400~1,000